

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,126,179 B2
APPLICATION NO. : 10/758102
DATED : October 24, 2006
INVENTOR(S) : Li Li et al.

Page 1 of 5

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In Item (74) *Attorney, Agent, or Firm* -- on the patent cover:

“Dickstein ShapiroLL” should read --Dickstein Shapiro LLP--.

In Item (56) the Other Publications portion of the References Cited section:

“Adler, D., Moss, S.C., Amorphous memories and bistable swithces, J. Vac. Sci. Technol. 9 (1972) 1182-89.”

Should read

--Adler, D., Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-89.--;

“Aleksiejunas, A.; cesneys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171.”

Should read

--Aleksiejunas, A.; Cesneys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171.--;

“Boolchand, P.; Bresser, W.J., Compositional trends in glass transition temperature (T_g), network connectivitiy and nanoscale chemical phase separation in chalcogenides, Dept of ECECS, Univ. Cincinnati (Oct. 28, 199) 45221-0030.”

Should read

--Boolchand, P.; Bresser, W.J., Compositional trends in glass transition temperature (T_g), network connectivitiy and nanoscale chemical phase separation in chalcogenides, Dept. of ECECS, Univ. Cincinnati (Oct. 28, 1999) 45221-0030.--;

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It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

“Chen, G.; Cheng, J.; Chen, W., Effect of Si_3N_4 on chemically durability of chalcogenide glass, J. Non-Cryst. Solids 220 (1997) 249-253.”

Should read

--Chen, G.; Cheng, J.; Chen, W., Effect of Si_3N_4 on chemical durability of chalcogenide glass, J. Non-Cryst. Solids 220 (1997) 249-253.--;

“Choen, M.H.; Neale, R.G.; Paskin, A., A model for an amorphous semiconductor memory device, J. Non-Cryst. Solids 8-10 (1972) 885-891.”

Should read

--Cohen, M.H.; Neale, R.G.; Paskin, A., A model for an amorphous semiconductor memory device, J. Non-Cryst. Solids 8-10 (1972) 885-891.--;

“Drusedau, T.P.; Panckow, A.N.; Klabunde, F., The hydrogenated amorphous silicon/nanodisperse metal (SIMAL) system-Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832.”

Should read

--Drusedau, T.P.; Panckow, A.N.; Klabunde, F., The hydrogenated amorphous silicon/nanodisperse metal (SIMAL) system-Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832.--;

“El-Ghrandi, R.; Calas, J.; Galibert, G., Ag dissolution kinetics in amorphous $\text{GeSe}_{5.5}$ thin films from “in situ” resistance measurements vs. time, Phys. Stat. Sol. (a) 123 (1991) 451-4603”

Should read

--El-Ghrandi, R.; Calas, J.; Galibert, G., Ag dissolution kinetics in amorphous $\text{GeSe}_{5.5}$ thin films from “in situ” resistance measurements vs. time, Phys. Stat. Sol. (a) 123 (1991) 451-460.--;

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“Fischer-Colbrie, A.; Biennstock, A.; Fuoss, P.H.; Marcus, M.A., Structure and bonding in photodiffused amorphous Ag-GeSe₂ thin films, Rev. B 38 (1988) 12388-12403.”

Should read

--Fischer-Colbrie, A.; Bienenstock, A.; Fuoss, P.H.; Marcus, M.A., Structure and bonding in photodiffused amorphous Ag-GeSe₂ thin films, Phys. Rev. B 38 (1988) 12388-12403.--;

“Hajto, J.; McAuely, B.; Snell, A.J.; Owen, A.E., Theory of room temperature quantized resistance effects in metal-a-Si:H-metal thin film structures, J. Non-Cryst. Solids 198-200 (1996) 825-826.”

Should read

--Hajto, J.; McAuley, B.; Snell, A.J.; Owen, A.E., Theory of room temperature quantized resistance effects in metal-a-Si:H-metal thin film structures, J. Non-Cryst. Solids 198-200 (1996) 825- 826.--;

“Huggart et al., Development of silver sensitized germanium selenide photoresist, by reactive sputter etching in SF₆, 42 Appl. Phys. Lett. No.7, pp. 592-594 (Apr. 1983).”

Should read

--Huggett et al., Development of sliver sensitized germanium selenide photoresist by reactive sputter etching in SF₆, 42 Appl. Phys. Lett. No. 7, pp. 592-594 (Apr. 1983).--;

“Mchardy et al., The dissolution of metals in amorphous chalcogenides and the effects to electron and ultraviolet radiation, 20 J. Phys. C.: Solid State Phys., pp. 4055-4075 (1987)f.”

Should read

--McHardy et al., The dissolution of metals in amorphous chalcogenides and the effects of electron and ultraviolet radiation, 20 J. Phys. C.: Solid State Phys., pp. 4055-4075 (1987).--;

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“Mitkova, M.; Boolchand, P., Microscopic origin of the glass forming tendency in chalcogenides and constraint theory, J. Non-Cryst. Solids 240 (1998) 1-21.”

Should read

--Mitkova, M.; Boolchand, P., Microscopic origin of the glass forming tendency in chalcogenides and constraint theory, J. Non-Cryst. Solids 240 (1998) 1-21.--;

“Popov, A.I.; Geller, I.KH.; Shemetova, V.k., Memory and threshold switching effects in amorphous selenium, Phys. Stat. ol. (a) 44 (1977) K71-K73.”

Should read

--Popov, A.I.; Geller, I.KH.; Shemetova, V.K., Memory and threshold switching effects in amorphous selenium, Phys. Stat. Sol. (a) 44 (1977) K71-K73.--;

“Rose, M.J.; Hajto, J.; Lecomber, P.G.; Gage, S.M.; Choi, W.K.; Snel, A.J.; Owen, A.E., Amorphous silicon analogue memory devices, J. Non-Cryst Solids 115 (1989) 168-170.”

Should read

--Rose, M.J.; Hajto, J.; Lecomber, P.G.; Gage, S.M.; Choi, W.K.; Snell, A.J.; Owen, A.E., Amorphous silicon analogue memory devices, J. Non-Cryst Solids 115 (1989) 168-170.--;

“Sharma, P., Structural, electrical and optical properties of silver selenide films, Ond. J. Of pure and applied Phys. 35 (1997) 424-427.”

Should read

--Sharma, P., Structural, electrical and optical properties of silver selenide films, Ind. J. Of pure and applied phys. 35 (1997) 424-427.--; and

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“Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexper, H.; Lagarde, J.P.,
Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural
investigation, Transport-structure relations in fast ion and mixed conductors
Proceedings of the 6th Riso International symposium 9-13 Sep. 1985.”

Should read

--Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde,
J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural
investigation, Transport-structure relations in fast ion and mixed conductors
Proceedings of the 6th Riso International symposium 9-13 Sep. 1985.--.

Signed and Sealed this

Sixteenth Day of January, 2007

A handwritten signature in black ink, reading "Jon W. Dudas". The signature is stylized, with a large loop for the 'J' and a distinct 'D'.

JON W. DUDAS
Director of the United States Patent and Trademark Office